

IN THE CLAIMS

Please amend the Claims as follows:

1. (AMENDED) A method of fabricating a titanium
disilicide film in the manufacture of an integrated
circuit comprising:

providing a semiconductor substrate having silicon
5 regions to be silicided;

depositing a titanium layer directly overlying said
silicon regions to be silicided;

subjecting said substrate to a first annealing
whereby said titanium is transformed to phase C40
10 titanium disilicide where it overlies said silicon
regions and wherein said titanium not overlying said
silicon regions is unreacted;

subjecting said substrate to a second annealing
whereby phase C54 titanium disilicide is grown overlying
15 said phase C40 titanium disilicide and whereby said
phase C40 titanium disilicide is transformed to phase
C54 titanium disilicide; and

removing said unreacted titanium layer to complete
formation of said titanium disilicide film in the
20 manufacture of said integrated circuit.

8. (AMENDED) A method of fabricating a titanium disilicide film in the manufacture of an integrated circuit comprising:

providing a semiconductor substrate having silicon
5 regions to be silicided;

depositing a titanium layer directly overlying said silicon regions to be silicided;

subjecting said substrate to a laser annealing whereby said titanium is transformed to phase C40
10 titanium disilicide where it overlies said silicon regions and wherein said titanium not overlying said silicon regions is unreacted;

subjecting said substrate to a low temperature annealing whereby said phase C40 titanium disilicide is
15 grown overlying said phase C40 titanium disilicide and whereby said phase C40 titanium disilicide is transformed to phase C54 titanium disilicide; and

removing said unreacted titanium layer to complete formation of said titanium disilicide film in the
20 manufacture of said integrated circuit.

15. (AMENDED) A method of fabricating a titanium disilicide film in the manufacture of an integrated circuit comprising:

providing a semiconductor substrate having silicon